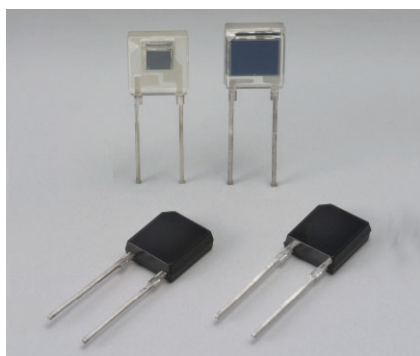


Si PIN photodiodes



S2506 series

S6775 series

S6967

Plastic SIP (single in-line package)

S2506/S6775 series and S6967 are Si PIN photodiodes with large active areas, molded into a clear or visible-cut plastic SIP for detecting visible to near infrared range or near infrared range only. These Si PIN photodiodes feature a high sensitivity, a high-speed response and large active areas.

Features

- **S2506-02: Visible to near infrared range**
S2506-04: Visible-cut
S6775, S6967: Visible to near infrared range, high sensitivity, high-speed response, large active area
- **S6775-01: Visible-cut, high sensitivity, high-speed response, large active area**
- **Plastic package: 7 × 7.8 mm**
- **Photosensitive area size**
S2506 series: 2.77 × 2.77 mm
S6775 series, S6967: 5.5 × 4.8 mm

Applications

- **FSO (free space optics)**
- **Optical switches**
- **Laser radar, etc.**

General ratings / Absolute maximum ratings

Type no.	Package	Photosensitive area size (mm)	Effective photosensitive area (mm ²)	Absolute maximum ratings			
				Reverse voltage V _R max. (V)	Power dissipation P (mW)	Operating temperature T _{opr} (°C)	Storage temperature T _{stg} (°C)
S2506-02	Plastic	2.77 × 2.77	7.7	35	150	-25 to +85	-40 to +100
S2506-04					50		
S6775		5.5 × 4.8	26.4		50		
S6775-01							
S6967							

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

Electrical and optical characteristics (Typ. T_a=25 °C, unless otherwise noted)

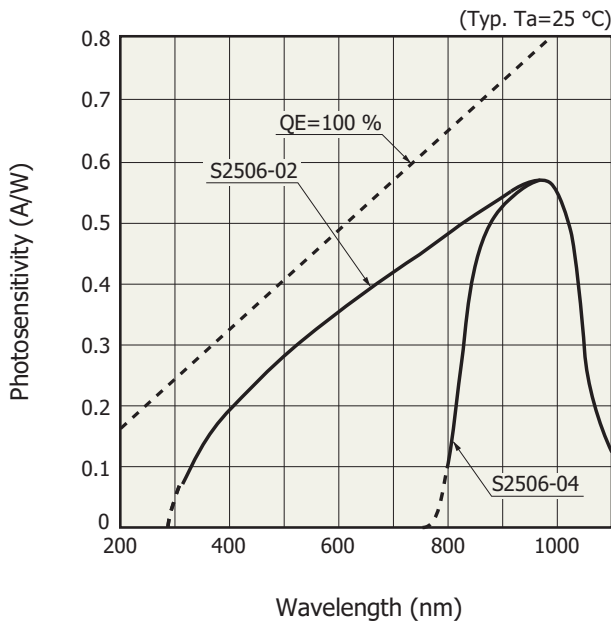
Type no.	Spectral response range λ (nm)	Peak sensitivity wavelength λ _p (nm)	Photosensitivity S (A/W)				Short circuit current I _{sc} 100 lx (μA)	Dark current I _D		Temp. coefficient of I _D T _{CI_D} (times/°C)	Cut-off frequency f _c R _L =50 Ω -3 dB (MHz)	Terminal capacitance C _t f=1 MHz (pF)	NEP (W/Hz ^{1/2})	
			λ _p	660 nm	780 nm	830 nm		Typ. (nA)	Max. (nA)					
S2506-02	320 to 1100	960	0.56	0.4	0.48	0.5	7.3	0.1*1	10*1	1.15	25*1	15*1	1.0 × 10 ^{-14*1}	
S2506-04	760 to 1100			-	-	0.25	4.1							
S6775	320 to 1100	960	0.7	0.45	0.55	0.6	30	0.5*2	10*2		15*2	40*2		1.8 × 10 ^{-14*2}
S6775-01	700 to 1100			0.68	-	0.48	0.54							21
S6967	320 to 1060			0.65	0.45	0.55	0.6				26	5*2		50*2

*1: V_R=12 V

*2: V_R=10 V

Spectral response

S2506 series



S6775 series, S6967

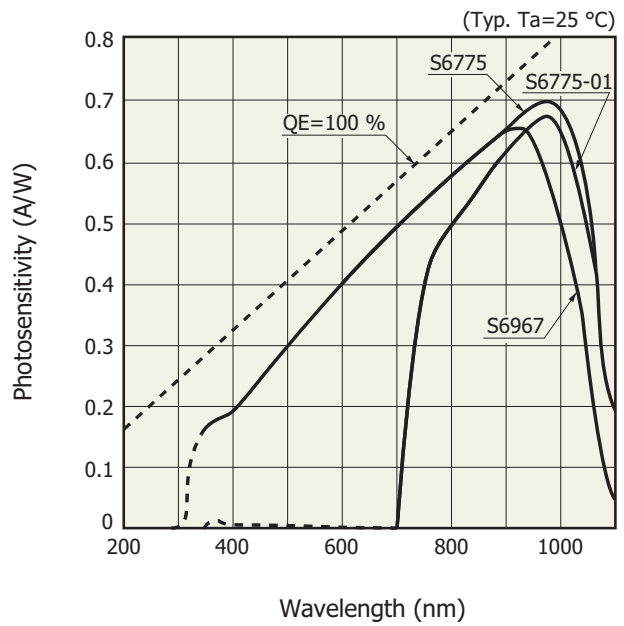
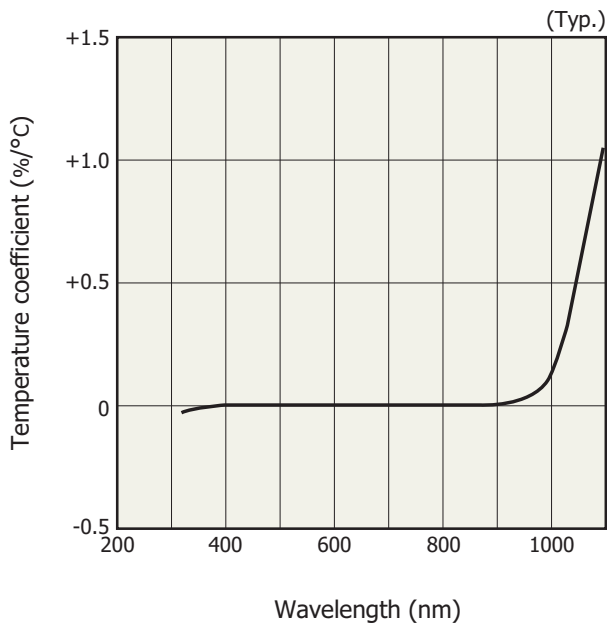
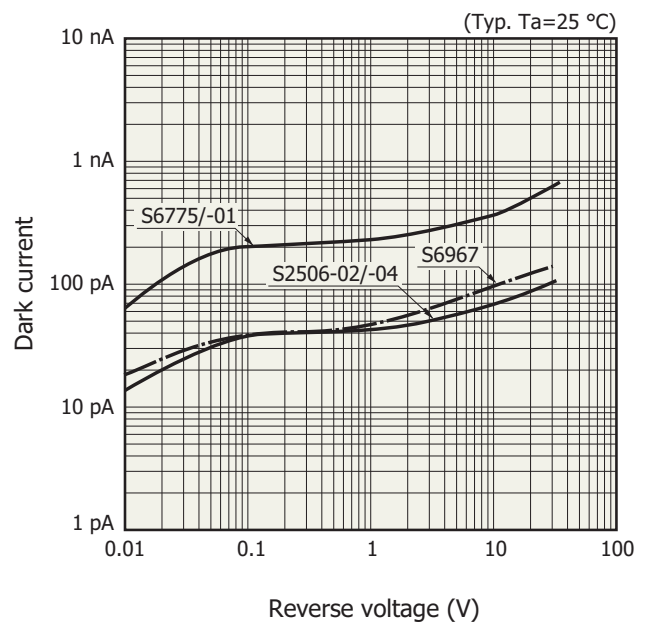


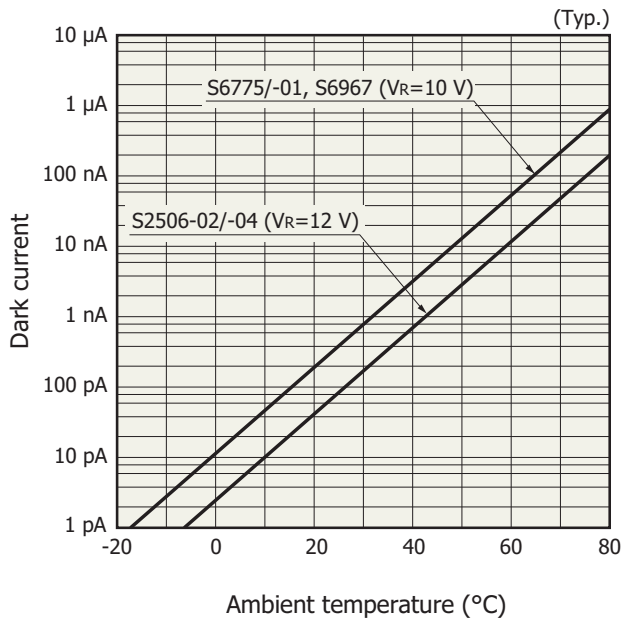
Photo sensitivity temperature characteristic (S2506-02)



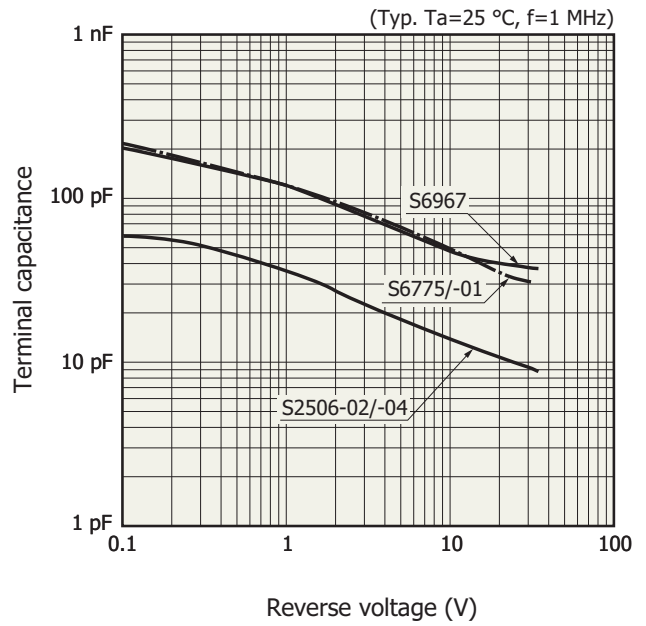
Dark current vs. reverse voltage



Dark current vs. ambient temperature

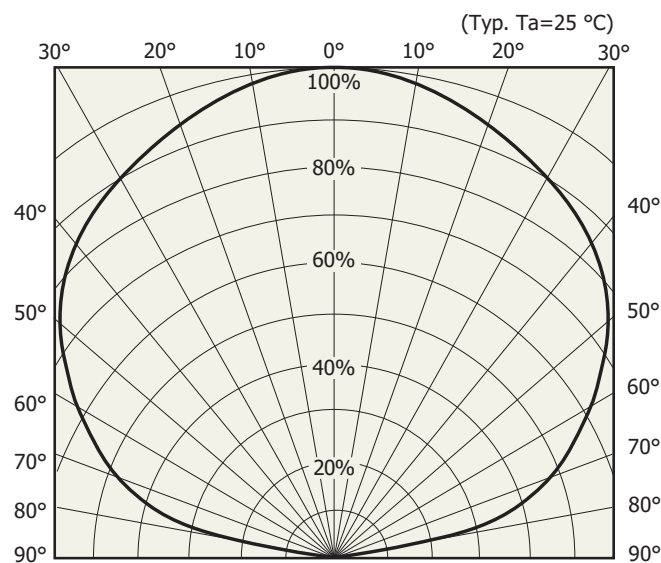


Terminal capacitance vs. reverse voltage



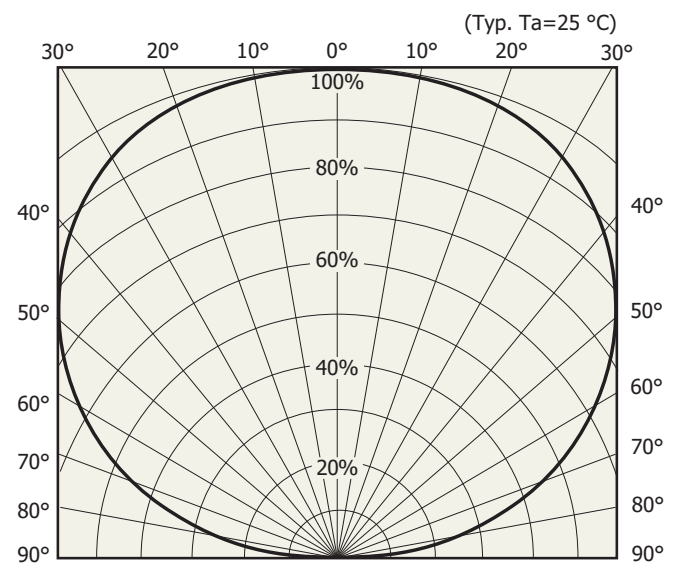
Directivity

S2506-02



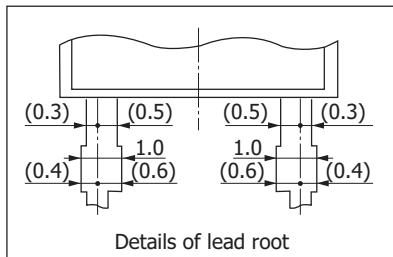
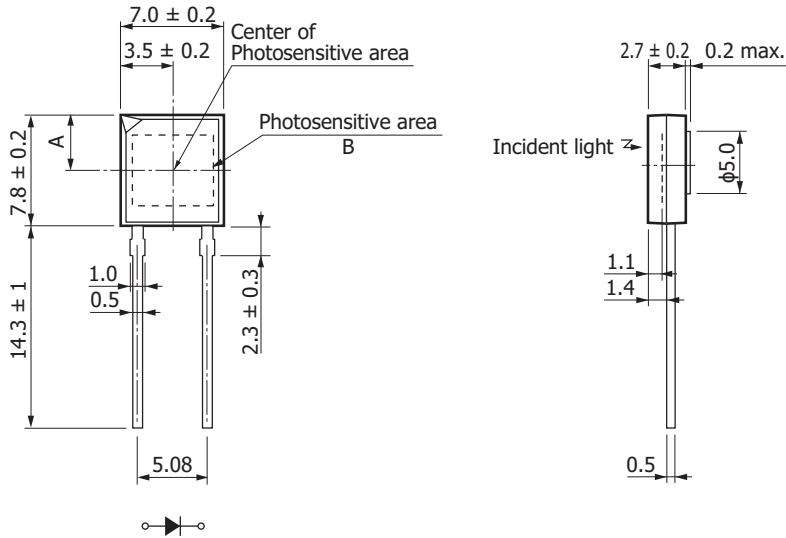
Relative sensitivity

S6775/-01, S6967



Relative sensitivity

Dimensional outline (unit: mm, tolerance unless otherwise noted: ±0.1)



Type no.	A	B
S2506 series	2.8 ± 0.2	2.77 × 2.77
S6775/series S6967	3.65 ± 0.2	5.5 × 4.8

Lead surface finish: Silver plating
 Packing: Polyethylene pack [anti-static type]
 (200 pcs/pack)

KPINA0084ED

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

■ Precautions

- Notice
- Metal, ceramic, plastic package products

■ Technical information

- Si photodiode/Application circuit examples

Information described in this material is current as of November, 2014.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use.

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